Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
<b>1</b> 1	1265	Semiconductor? and topology	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:00
L2	110	1 and ( aspect near2 ratio )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:01
L3	3	2 and ( electron near2 microscope )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:01
L4	5	2 and ( contact near2 hole? )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:01
L5	203	1 and ( inspect near4 hole or defect )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:02
L6	14	5 and ( electron near2 microscope )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:03
L7	4326	((250/310,492.2,) or (382/145, 149,)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/04 12:04
L8	3	7 and ( inspect near2 semiconductor? )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:05

L9	193	7 and ( aspect near2 ratio )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:05
L10	65	9 and ( inspect near4 semiconductor or defect )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:06
L11	. 25	10 and ( contact near2 hole )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:06
L12	19	11 and ( electron near2 microscope )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:07
L13	9	"6,373,054"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:07

1/4/05 " Method Hits Search Query DBs **Plurals** Ref Default Time Stamp Operator # L1 1265 Semiconductor? and topology US-PGPUB; AND OFF 2005/01/04 12:00 USPAT: USOCR; EPO; JPO; DERWENT; IBM\_TDB L2 110 1 and (aspect near2 ratio) US-PGPUB; AND OFF 2005/01/04 12:01 USPAT; USOCR; EPO; JPO; DERWENT: IBM\_TDB 2 and ( electron near2 microscope L3 US-PGPUB; AND OFF 2005/01/04 12:01 USPAT; USOCR; EPO; JPO; DERWENT; IBM\_TDB US-PGPUB; L4 2 and (contact near2 hole?) AND OFF 2005/01/04 12:01 USPAT; USOCR; EPO; JPO; DERWENT; IBM\_TDB L5 203 OFF 1 and (inspect near4 hole or US-PGPUB: 2005/01/04 12:02 AND defect ) USPAT; USOCR; EPO; JPO; DERWENT; IBM\_TDB L6 5 and ( electron near2 microscope **US-PGPUB**; OFF 14 AND 2005/01/04 12:03 USPAT; USOCR; EPO; JPO; **DERWENT**; IBM\_TDB US-PGPUB; OFF L7 4326 ((250/310,492.2,) or (382/145, OR 2005/01/04 12:04 149,)).CCLS. USPAT; USOCR US-PGPUB; 2005/01/04 12:05 L8 3 7 and (inspect near2 AND OFF semiconductor?) USPAT; USOCR; EPO; JPO; DERWENT;

IBM\_TDB

10/614,825

L9	193	7 and ( aspect near2 ratio )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:05
L10	65	9 and ( inspect near4 semiconductor or defect )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:06
L11	25	10 and ( contact near2 hole )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:06
L12	19	11 and ( electron near2 microscope )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:07
L13	9	"6,373,054"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:07